



# Advanced Single-Channel Gate Driver for Insulated Gate Bipolar Transistors and Silicon Carbide MOSFETs

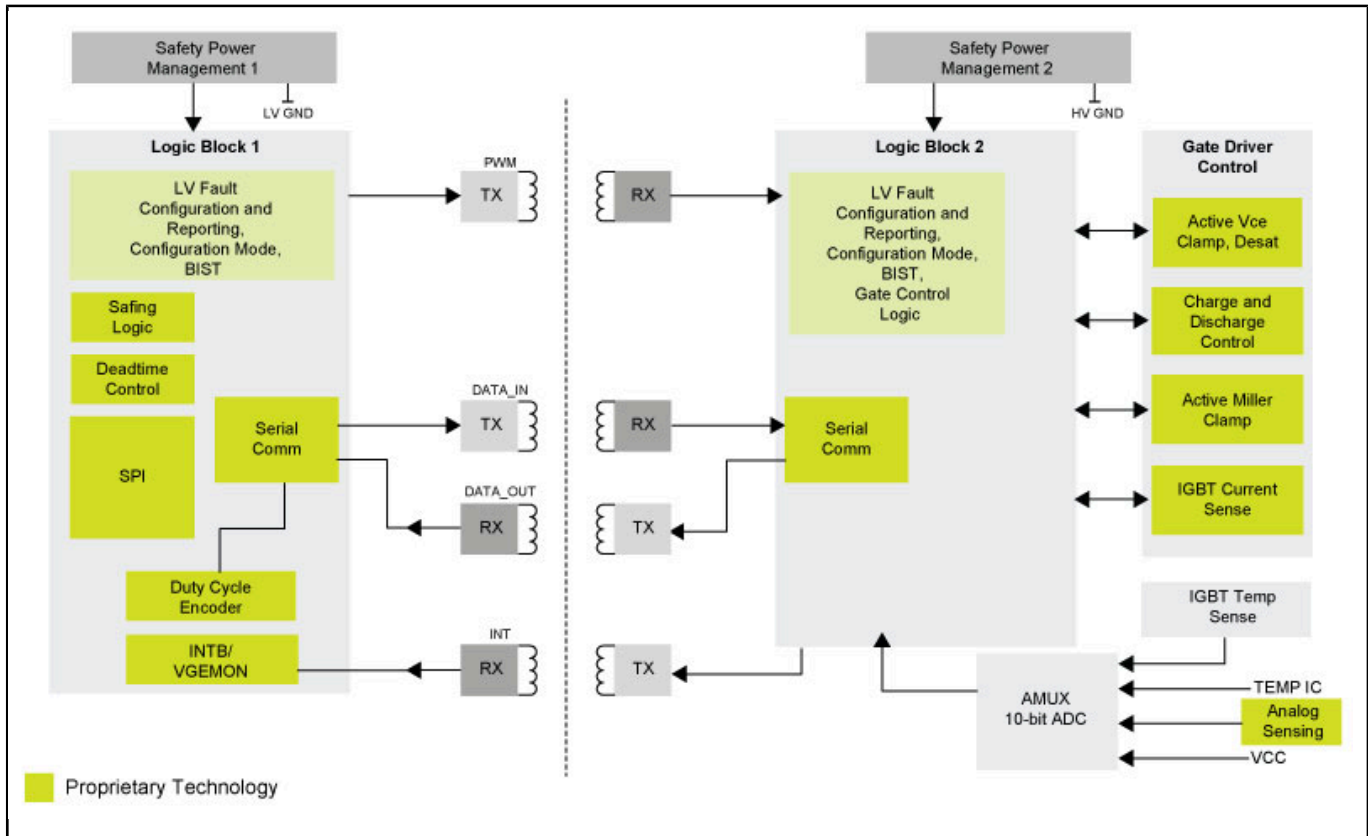
## GD3100

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The GD3100 is an advanced single-channel gate driver for IGBTs/SiC. Integrated Galvanic isolation and low on-resistance drive transistors provide high charging and discharging current, low dynamic saturation voltage and rail-to-rail gate voltage control.

- Current and temperature sense minimizes IGBT/SiC stress during faults
- Accurate and configurable under voltage lockout provides protection while ensuring sufficient gate drive voltage headroom
- Autonomously manages severe faults and reports faults and status via INTB pin and an SPI interface. It is capable of directly driving gates of many IGBTs/SiC
- Self-test, control and protection functions are included for the design of high-reliability systems

## GD3100, Advanced IGBT/SiC Gate Driver - Block Diagram Block Diagram



View additional information for [Advanced Single-Channel Gate Driver for Insulated Gate Bipolar Transistors and Silicon Carbide MOSFETs](#).

**Note:** The information on this document is subject to change without notice.

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